2SB1219

Silicon PNP epitaxial planar type

For general amplification
Complementary to 2SD1820

■ Features

- Large collector current I_C
- S-Mini type package, allowing downsizing of the equipment and automatic insertion through the tape packing.

■ Package

- Code
  SMini3-G1
- Pin Name
  1. Base
  2. Emitter
  3. Collector

■ Marking Symbol: C

■ Absolute Maximum Ratings $T_a = 25°C$

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	V_{CBO}	–30	V
Collector-emitter voltage (Base open)	V_{CEO}	–25	V
Emitter-base voltage (Collector open)	V_{EBO}	–5	V
Collector current	I_C	–500	mA
Peak collector current	I_{CP}	–1	A
Collector power dissipation	P_C	150	mW
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	–55 to +150	°C

■ Electrical Characteristics $T_a = 25°C \pm 3°C$

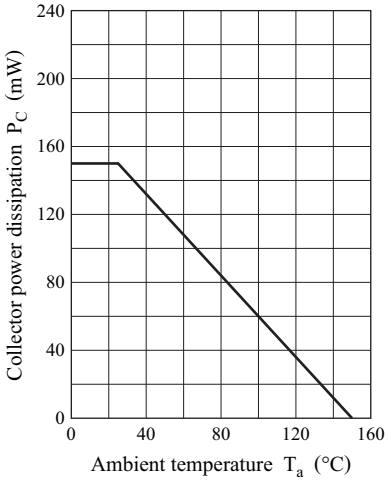
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-base voltage (Emitter open)	V_{CBO}	$I_C = -10$ μA, $I_E = 0$	–30			V
Collector-emitter voltage (Base open)	V_{CEO}	$I_C = -2$ mA, $I_B = 0$	–25			V
Emitter-base voltage (Collector open)	V_{EBO}	$I_E = -10$ μA, $I_C = 0$	–5			V
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{CB} = -20$ V, $I_E = 0$			– 0.1	μA
Forward current transfer ratio *1	h_{FE1} *2	$V_{CE} = -10$ V, $I_C = -150$ mA	85		340	—
	h_{FE2}	$V_{CE} = -10$ V, $I_C = -500$ mA	40			
Collector-emitter saturation voltage *1	$V_{CE(sat)}$	$I_C = -300$ mA, $I_B = -30$ mA		– 0.35	– 0.60	V
Base-emitter saturation voltage *1	$V_{BE(sat)}$	$I_C = -300$ mA, $I_B = -30$ mA		–1.1	–1.5	V
Transition frequency	f_T	$V_{CB} = -10$ V, $I_E = 50$ mA, f = 200 MHz		200		MHz
Collector output capacitance (Common base, input open circuited)	C_{ob}	$V_{CB} = -10$ V, $I_E = 0$, f = 1 MHz		6	15	pF

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.
2. *1: Pulse measurement
*2: Rank classification

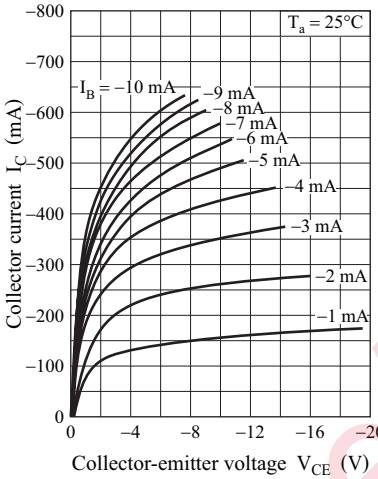
Rank	Q	R	S	No-rank
h_{FE1}	85 to 170	120 to 240	170 to 340	85 to 340
Marking symbol	CQ	CR	CS	C

Product of no-rank is not classified and have no marking symbol for rank.

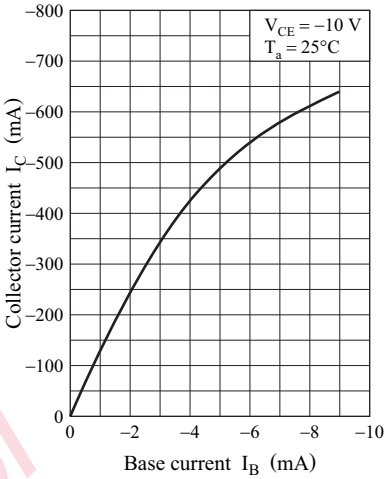
P_C — T_a



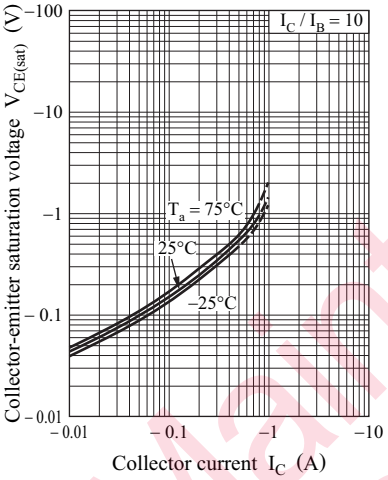
I_C — V_{CE}



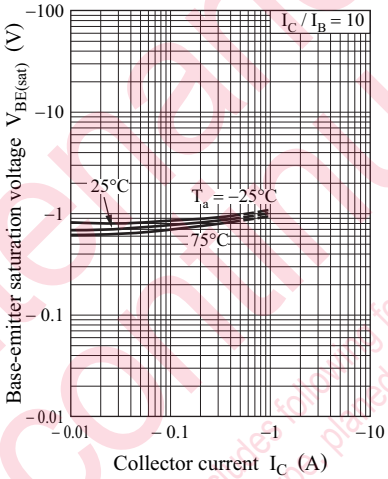
I_C — I_B



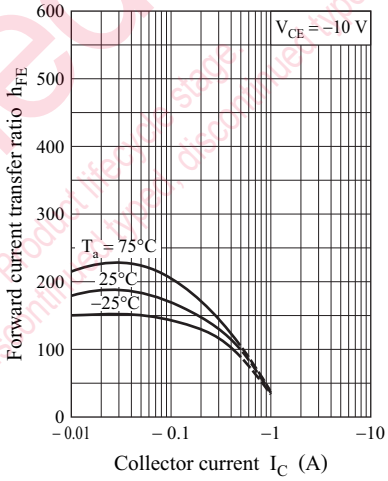
$V_{CE(sat)}$ — I_C



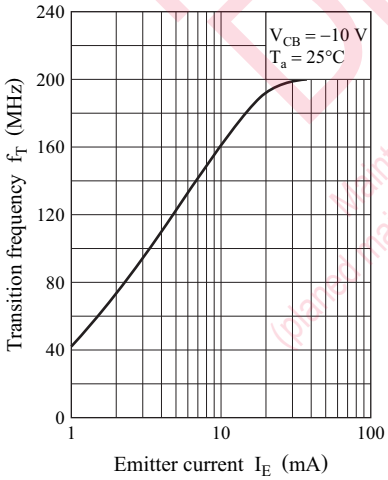
$V_{BE(sat)}$ — I_C



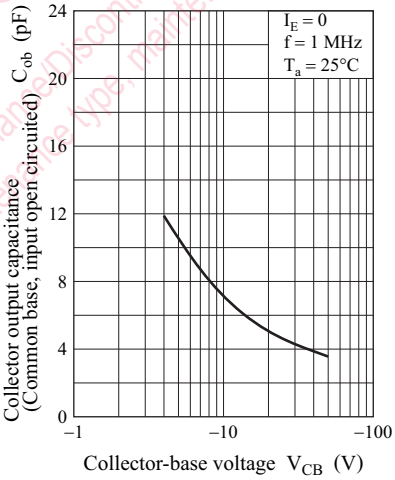
h_{FE} — I_C



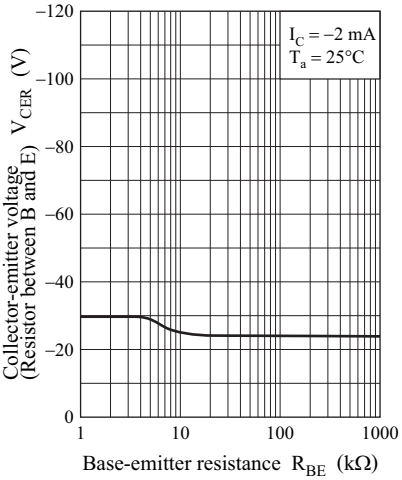
f_T — I_E



C_{ob} — V_{CB}

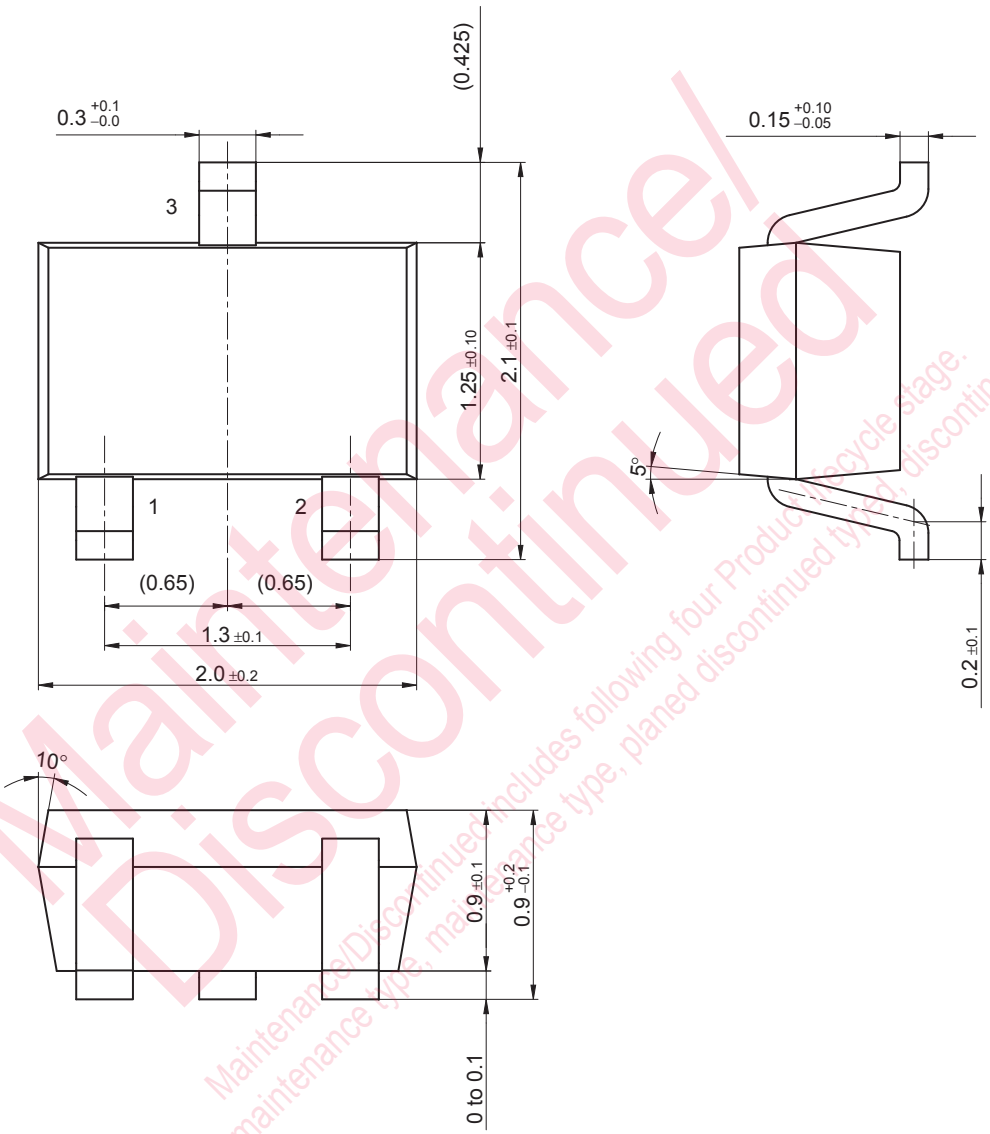


V_{CER} — R_{BE}



SMini3-G1

Unit: mm



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